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#### Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

#### Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

#### Details

Obsolete
PowerPC e500
1 Core, 32-Bit
1.0GHz
Signal Processing; SPE, Security; SEC
DDR, DDR2, SDRAM
No
-
10/100/1000Mbps (2)
-
-
1.8V, 2.5V, 3.3V
0°C ~ 105°C (TA)
Cryptography, Random Number Generator
783-BBGA, FCBGA
783-FCPBGA (29x29)
https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8544eavtaqg

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

# NP

MPC8544E Overview

- Double-precision floating-point APU. Provides an instruction set for double-precision (64-bit) floating-point instructions that use the 64-bit GPRs.
- 36-bit real addressing
- Embedded vector and scalar single-precision floating-point APUs. Provide an instruction set for single-precision (32-bit) floating-point instructions.
- Memory management unit (MMU). Especially designed for embedded applications. Supports 4-Kbyte–4-Gbyte page sizes.
- Enhanced hardware and software debug support
- Performance monitor facility that is similar to, but separate from, the device performance monitor

The e500 defines features that are not implemented on this device. It also generally defines some features that this device implements more specifically. An understanding of these differences can be critical to ensure proper operations.

- 256-Kbyte L2 cache/SRAM
  - Flexible configuration
  - Full ECC support on 64-bit boundary in both cache and SRAM modes
  - Cache mode supports instruction caching, data caching, or both.
  - External masters can force data to be allocated into the cache through programmed memory ranges or special transaction types (stashing).
    - 1, 2, or 4 ways can be configured for stashing only.
  - Eight-way set-associative cache organization (32-byte cache lines)
  - Supports locking entire cache or selected lines. Individual line locks are set and cleared through Book E instructions or by externally mastered transactions.
  - Global locking and flash clearing done through writes to L2 configuration registers
  - Instruction and data locks can be flash cleared separately.
  - SRAM features include the following:
    - I/O devices access SRAM regions by marking transactions as snoopable (global).
    - Regions can reside at any aligned location in the memory map.
    - Byte-accessible ECC is protected using read-modify-write transaction accesses for smaller-than-cache-line accesses.
- Address translation and mapping unit (ATMU)
  - Eight local access windows define mapping within local 36-bit address space.
  - Inbound and outbound ATMUs map to larger external address spaces.
    - Three inbound windows plus a configuration window on PCI and PCI Express
    - Four outbound windows plus default translation for PCI and PCI Express
- DDR/DDR2 memory controller
  - Programmable timing supporting DDR and DDR2 SDRAM
  - 64-bit data interface



- Four banks of memory supported, each up to 4 Gbytes, to a maximum of 16 Gbytes
- DRAM chip configurations from 64 Mbits to 4 Gbits with x8/x16 data ports
- Full ECC support
- Page mode support
  - Up to 16 simultaneous open pages for DDR
  - Up to 32 simultaneous open pages for DDR2
- Contiguous or discontiguous memory mapping
- Sleep mode support for self-refresh SDRAM
- On-die termination support when using DDR2
- Supports auto refreshing
- On-the-fly power management using CKE signal
- Registered DIMM support
- Fast memory access via JTAG port
- 2.5-V SSTL\_2 compatible I/O (1.8-V SSTL\_1.8 for DDR2)
- Programmable interrupt controller (PIC)
  - Programming model is compliant with the OpenPIC architecture.
  - Supports 16 programmable interrupt and processor task priority levels
  - Supports 12 discrete external interrupts
  - Supports 4 message interrupts with 32-bit messages
  - Supports connection of an external interrupt controller such as the 8259 programmable interrupt controller
  - Four global high resolution timers/counters that can generate interrupts
  - Supports a variety of other internal interrupt sources
  - Supports fully nested interrupt delivery
  - Interrupts can be routed to external pin for external processing.
  - Interrupts can be routed to the e500 core's standard or critical interrupt inputs.
  - Interrupt summary registers allow fast identification of interrupt source.
- Integrated security engine (SEC) optimized to process all the algorithms associated with IPSec, IKE, WTLS/WAP, SSL/TLS, and 3GPP
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Dynamic assignment of crypto-execution units via an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
  - PKEU—public key execution unit
    - RSA and Diffie-Hellman; programmable field size up to 2048 bits
    - Elliptic curve cryptography with  $F_2m$  and F(p) modes and programmable field size up to 511 bits
  - DEU—Data Encryption Standard execution unit
    - DES, 3DES



MPC8544E Overview

- Broadcast address (accept/reject)
- Hash table match on up to 512 multicast addresses
- Promiscuous mode
- Buffer descriptors backward compatible with MPC8260 and MPC860T 10/100 Ethernet programming models
- RMON statistics support
- 10-Kbyte internal transmit and 2-Kbyte receive FIFOs
- MII management interface for control and status
- Ability to force allocation of header information and buffer descriptors into L2 cache
- OCeaN switch fabric
  - Full crossbar packet switch
  - Reorders packets from a source based on priorities
  - Reorders packets to bypass blocked packets
  - Implements starvation avoidance algorithms
  - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
  - Four-channel controller
  - All channels accessible by both the local and remote masters
  - Extended DMA functions (advanced chaining and striding capability)
  - Support for scatter and gather transfers
  - Misaligned transfer capability
  - Interrupt on completed segment, link, list, and error
  - Supports transfers to or from any local memory or I/O port
  - Selectable hardware-enforced coherency (snoop/no snoop)
  - Ability to start and flow control each DMA channel from external 3-pin interface
  - Ability to launch DMA from single write transaction
- PCI controller
  - PCI 2.2 compatible
  - One 32-bit PCI port with support for speeds from 16 to 66 MHz
  - Host and agent mode support
  - 64-bit dual address cycle (DAC) support
  - Supports PCI-to-memory and memory-to-PCI streaming
  - Memory prefetching of PCI read accesses
  - Supports posting of processor-to-PCI and PCI-to-memory writes
  - PCI 3.3-V compatible
  - Selectable hardware-enforced coherency



DDR and DDR2 SDRAM

# 6.2.2 DDR SDRAM Output AC Timing Specifications

Table 18 provides the output AC timing specifications for the DDR SDRAM interface.

#### Table 18. DDR SDRAM Output AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol <sup>1</sup>	Min	Мах	Unit	Notes
MCK[n] cycle time, MCK[n]/MCK[n] crossing	t <sub>MCK</sub>	3.75	6	ns	2
ADDR/CMD output setup with respect to MCK	t <sub>DDKHAS</sub>			ns	3
533 MHz 400 MHz 333 MHz		1.48 1.95 2.40			7
ADDR/CMD output hold with respect to MCK	t <sub>DDKHAX</sub>			ns	3
533 MHz 400 MHz 333 MHz		1.48 1.95 2.40			7 
MCS[n] output setup with respect to MCK	t <sub>DDKHCS</sub>			ns	3
533 MHz 400 MHz 333 MHz		1.48 1.95 2.40			7 
MCS[n] output hold with respect to MCK	t <sub>DDKHCX</sub>			ns	3
533 MHz 400 MHz 333 MHz		1.48 1.95 2.40			7 
MCK to MDQS Skew	t <sub>DDKHMH</sub>	-0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS	<sup>t</sup> DDKHDS, t <sub>DDKLDS</sub>			ps	5
533 MHz 400 MHz 333 MHz		538 700 900			7 
MDQ/MECC/MDM output hold with respect to MDQS	t <sub>DDKHDX,</sub> t <sub>DDKLDX</sub>			ps	5
533 MHz 400 MHz 333 MHz		538 700 900			7 — —
MDQS preamble	t <sub>DDKHMP</sub>	0.75 x tMCK	—	ns	6



#### Table 33. MII Receive AC Timing Specifications (continued)

At recommended operating conditions with L/TVDD of 3.3 V  $\pm$  5%.or 2.5 V  $\pm$  5%.

Parameter/Condition	Symbol <sup>1</sup>	Min	Тур	Мах	Unit	Notes
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t <sub>MRDVKH</sub>	10.0	—	—	ns	—
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t <sub>MRDXKH</sub>	10.0	—	—	ns	—
RX_CLK clock rise (20%–80%)	t <sub>MRXR</sub>	1.0	—	4.0	ns	—
RX_CLK clock fall time (80%–20%)	t <sub>MRXF</sub>	1.0	—	4.0	ns	

#### Note:

1. The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t<sub>(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t<sub>MRDVKH</sub> symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t<sub>MRX</sub> clock reference (K) going to the high (H) state or setup time. Also, t<sub>MRDXKL</sub> symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t<sub>MRX</sub> clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t<sub>MRX</sub> represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).</sub></sub>

Figure 17 provides the AC test load for eTSEC.



Figure 17. eTSEC AC Test Load

Figure 18 shows the MII receive AC timing diagram.



Figure 18. MII Receive AC Timing Diagram

# 8.7 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.



Enhanced Three-Speed Ethernet (eTSEC), MII Management

# 8.7.5 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

### 8.7.5.1 RMII Transmit AC Timing Specifications

The RMII transmit AC timing specifications are in Table 38.

#### Table 38. RMII Transmit AC Timing Specifications

At recommended operating conditions with L/TV<sub>DD</sub> of 3.3 V  $\pm$  5% or 2.5 V  $\pm$  5%.

Parameter/Condition	Symbol <sup>1</sup>	Min	Тур	Мах	Unit	Notes
REF_CLK clock period	t <sub>RMT</sub>	15.0	20.0	25.0	ns	—
REF_CLK duty cycle	t <sub>RMTH</sub>	35	50	65	%	—
REF_CLK peak-to-peak jitter	t <sub>RMTJ</sub>	_	_	250	ps	—
Rise time REF_CLK (20%–80%)	t <sub>RMTR</sub>	1.0	_	2.0	ns	—
Fall time REF_CLK (80%–20%)	t <sub>RMTF</sub>	1.0	_	2.0	ns	—
REF_CLK to RMII data TXD[1:0], TX_EN delay	t <sub>RMTDX</sub>	1.0	_	10.0	ns	—

#### Note:

The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t<sub>(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t<sub>MTKHDX</sub> symbolizes MII transmit timing (MT) for the time t<sub>MTX</sub> clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t<sub>MTX</sub> represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
</sub></sub>

#### Figure 23 shows the RMII transmit AC timing diagram.



Figure 23. RMII Transmit AC Timing Diagram



Table 41. MII Management AC Timing Specifications (continued)

At recommended operating conditions with  $\text{OV}_{\text{DD}}$  is 3.3 V  $\pm$  5%.

Parameter/Condition	Symbol <sup>1</sup>	Min	Тур	Мах	Unit	Notes
MDC fall time	t <sub>MDHF</sub>	_	_	10	ns	

#### Notes:

The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t<sub>(first two letters of functional block)</sub>(reference)(state)(signal)(state) for outputs. For example, t<sub>MDKHDX</sub> symbolizes management data timing (MD) for the time t<sub>MDC</sub> from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t<sub>MDDVKH</sub> symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t<sub>MDC</sub> clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
</sub>

- 2. This parameter is dependent on the platform clock frequency (MIIMCFG [MgmtClk] field determines the clock frequency of the MgmtClk Clock EC\_MDC).
- 3. This parameter is dependent on the platform clock frequency. The delay is equal to 16 platform clock periods ±3 ns. For example, with a platform clock of 333 MHz, the min/max delay is 48 ns ± 3 ns. Similarly, if the platform clock is 400 MHz, the min/max delay is 40 ns ± 3 ns).
- 4. t<sub>plb clk</sub> is the platform (CCB) clock.

Figure 26 shows the MII management AC timing diagram.



Figure 26. MII Management Interface Timing Diagram



Parameter	Symbol	Min	Мах	Unit	Notes
High-level output voltage (BV <sub>DD</sub> = min, I <sub>OH</sub> = -2 mA)	V <sub>OH</sub>	1.35	_	V	
Low-level output voltage (BV <sub>DD</sub> = min, I <sub>OL</sub> = 2 mA)	V <sub>OL</sub>		0.45	V	

Table 44. Local Bus DC Electrical Characteristics (1.8 V DC) (continued)

# **10.2 Local Bus AC Electrical Specifications**

Table 45 describes the general timing parameters of the local bus interface at  $BV_{DD} = 3.3$  V. For information about the frequency range of local bus see Section 19.1, "Clock Ranges."

Parameter	Symbol <sup>1</sup>	Min	Мах	Unit	Notes
Local bus cycle time	t <sub>LBK</sub>	7.5	12	ns	2
Local bus duty cycle	t <sub>LBKH/</sub> t <sub>LBK</sub>	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	t <sub>LBKSKEW</sub>	—	150	ps	7, 8
Input setup to local bus clock (except LUPWAIT)	t <sub>LBIVKH1</sub>	2.5	—	ns	3, 4
LUPWAIT input setup to local bus clock	t <sub>LBIVKH2</sub>	1.85	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	t <sub>LBIXKH1</sub>	1.0	—	ns	3, 4
LUPWAIT input hold from local bus clock	t <sub>LBIXKH2</sub>	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	t <sub>lbotot</sub>	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	t <sub>LBKHOV1</sub>	—	2.9	ns	—
Local bus clock to data valid for LAD/LDP	t <sub>LBKHOV2</sub>	—	2.8	ns	—
Local bus clock to address valid for LAD	t <sub>LBKHOV3</sub>	—	2.7	ns	3
Local bus clock to LALE assertion	t <sub>LBKHOV4</sub>	—	2.7	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	t <sub>LBKHOX1</sub>	0.7	—	ns	3
Output hold from local bus clock for LAD/LDP	t <sub>LBKHOX2</sub>	0.7	_	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	t <sub>LBKHOZ1</sub>	—	2.5	ns	5

Table 45. Local Bus General Timing Parameters (BV<sub>DD</sub> = 3.3 V)—PLL Enabled



#### Table 46. Local Bus General Timing Parameters (BV<sub>DD</sub> = 2.5 V)—PLL Enabled (continued)

Parameter	Symbol <sup>1</sup>	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	t <sub>LBKHOZ2</sub>	_	2.6	ns	5

Notes:

The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t<sub>(First two letters of functional block)(reference)(state)(signal)(state)</sub> for outputs. For example, t<sub>LBIXKH1</sub> symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t<sub>LBK</sub> clock reference (K) goes high (H), in this case for clock one (1). Also, t<sub>LBKHOX</sub> symbolizes local bus timing (LB) for the t<sub>LBK</sub> clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
</sub>

2. All timings are in reference to LSYNC\_IN for PLL enabled and internal local bus clock for PLL bypass mode.

3. All signals are measured from  $BV_{DD}/2$  of the rising edge of LSYNC\_IN for PLL enabled or internal local bus clock for PLL bypass mode to 0.4 ×  $BV_{DD}$  of the signal in question for 2.5-V signaling levels.

4. Input timings are measured at the pin.

5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

- 6. t<sub>LBOTOT</sub> is a measurement of the minimum time between the negation of LALE and any change in LAD. t<sub>LBOTOT</sub> is programmed with the LBCR[AHD] parameter.
- 7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at BV<sub>DD</sub>/2.

Table 47	describes the	general timing	parameters of the	local bus inter	face at $BV_{DD} =$	1.8 V DC.
		L) L.			1717	

Parameter	Symbol <sup>1</sup>	Min	Мах	Unit	Notes
Local bus cycle time	t <sub>LBK</sub>	7.5	12	ns	2
Local bus duty cycle	t <sub>LBKH/</sub> t <sub>LBK</sub>	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	t <sub>lbkskew</sub>	—	150	ps	7
Input setup to local bus clock (except LUPWAIT)	t <sub>LBIVKH1</sub>	2.6	—	ns	3, 4
LUPWAIT input setup to local bus clock	t <sub>LBIVKH2</sub>	1.9	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	t <sub>LBIXKH1</sub>	1.1	—	ns	3, 4
LUPWAIT input hold from local bus clock	t <sub>LBIXKH2</sub>	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	t <sub>lbotot</sub>	1.2	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	t <sub>LBKHOV1</sub>	—	3.2	ns	_
Local bus clock to data valid for LAD/LDP	t <sub>LBKHOV2</sub>	—	3.2	ns	3
Local bus clock to address valid for LAD	t <sub>LBKHOV3</sub>	—	3.2	ns	3
Local bus clock to LALE assertion	t <sub>LBKHOV4</sub>	—	3.2	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	t <sub>LBKHOX1</sub>	0.9	—	ns	3
Output hold from local bus clock for LAD/LDP	t <sub>LBKHOX2</sub>	0.9	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	t <sub>LBKHOZ1</sub>	_	2.6	ns	5

#### Table 47. Local Bus General Timing Parameters (BV<sub>DD</sub> = 1.8 V DC)



JTAG

# 12 JTAG

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the MPC8544E.

# 12.1 JTAG DC Electrical Characteristics

Table 49 provides the DC electrical characteristics for the JTAG interface.

### Table 49. JTAG DC Electrical Characteristics

Parameter	Symbol	Min	Мах	Unit	Notes
High-level input voltage	V <sub>IH</sub>	2	OV <sub>DD</sub> + 0.3	V	
Low-level input voltage	V <sub>IL</sub>	-0.3	0.8	V	
Input current (OV <sub>IN</sub> = 0 V or OV <sub>IN</sub> = OV <sub>DD</sub> )	I <sub>IN</sub>	—	±5	μA	1
High-level output voltage ( $OV_{DD} = min, I_{OH} = -2 mA$ )	V <sub>OH</sub>	2.4	—	V	_
Low-level output voltage ( $OV_{DD} = min, I_{OL} = 2 mA$ )	V <sub>OL</sub>	—	0.4	V	_

Note:

1. Note that the symbol  $V_{IN}$ , in this case, represents the  $OV_{IN}$ .

# **12.2 JTAG AC Electrical Specifications**

Table 50 provides the JTAG AC timing specifications as defined in Figure 34 through Figure 37.

### Table 50. JTAG AC Timing Specifications (Independent of SYSCLK)<sup>1</sup>

At recommended operating conditions (see Table 3).

Parameter	Symbol <sup>2</sup>	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f <sub>JTG</sub>	0	33.3	MHz	—
JTAG external clock cycle time	t <sub>JTG</sub>	30	_	ns	—
JTAG external clock pulse width measured at 1.4 V	t <sub>JTKHKL</sub>	15	—	ns	—
JTAG external clock rise and fall times	t <sub>JTGR</sub> & t <sub>JTGF</sub>	0	2	ns	—
TRST assert time	t <sub>TRST</sub>	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t <sub>JTDVKH</sub> t <sub>JTIVKH</sub>	4 0		ns	4
Input hold times: Boundary-scan data TMS, TDI	t <sub>JTDXKH</sub> t <sub>JTIXKH</sub>	20 25	_	ns	4
Valid times: Boundary-scan data TDO	t <sub>JTKLDV</sub> t <sub>JTKLOV</sub>	4 4	20 25	ns	5
Output hold times: Boundary-scan data TDO	t <sub>jtkldx</sub> t <sub>jtklox</sub>	2.5 4		ns	5



PCI

# 15.2 PCI AC Electrical Specifications

This section describes the general AC timing parameters of the PCI bus. Note that the SYSCLK signal is used as the PCI input clock. Table 56 provides the PCI AC timing specifications at 66 MHz.

Parameter	Symbol <sup>1</sup>	Min	Max	Unit	Notes
SYSCLK to output valid	t <sub>PCKHOV</sub>	_	7.4	ns	2, 3
Output hold from SYSCLK	t <sub>PCKHOX</sub>	2.0	_	ns	2
SYSCLK to output high impedance	t <sub>PCKHOZ</sub>	_	14	ns	2, 4
Input setup to SYSCLK	t <sub>PCIVKH</sub>	3.7	_	ns	2, 5
Input hold from SYSCLK	t <sub>PCIXKH</sub>	0.5	_	ns	2, 5
REQ64 to HRESET <sup>9</sup> setup time	t <sub>PCRVRH</sub>	$10 \times t_{SYS}$	_	clocks	6, 7
HRESET to REQ64 hold time	t <sub>PCRHRX</sub>	0	50	ns	7
HRESET high to first FRAME assertion	t <sub>PCRHFV</sub>	10	_	clocks	8
Rise time (20%–80%)	t <sub>PCICLK</sub>	0.6	2.1	ns	
Fall time (20%–80%)	t <sub>PCICLK</sub>	0.6	2.1	ns	

Table 56. PCI AC Timin	g Specifications at 66 MHz
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Notes:

The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t<sub>(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t<sub>PCIVKH</sub> symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the SYSCLK clock, t<sub>SYS</sub>, reference (K) going to the high (H) state or setup time. Also, t<sub>PCRHFV</sub> symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
</sub></sub>

- 2. See the timing measurement conditions in the PCI 2.2 Local Bus Specifications.
- 3. All PCI signals are measured from  $OV_{DD}/2$  of the rising edge of PCI\_SYNC\_IN to  $0.4 \times OV_{DD}$  of the signal in question for 3.3-V PCI signaling levels.
- 4. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- 5. Input timings are measured at the pin.
- The timing parameter t<sub>SYS</sub> indicates the minimum and maximum CLK cycle times for the various specified frequencies. The system clock period must be kept within the minimum and maximum defined ranges. For values see Section 19, "Clocking."
- 7. The setup and hold time is with respect to the rising edge of HRESET.
- 8. The timing parameter t<sub>PCRHFV</sub> is a minimum of 10 clocks rather than the minimum of 5 clocks in the PCI 2.2 Local Bus Specifications.
- 9. The reset assertion timing requirement for  $\overline{\text{HRESET}}$  is 100  $\mu\text{s}.$

Figure 41 provides the AC test load for PCI.



Figure 41. PCI AC Test Load



### 16.2.4 AC Requirements for SerDes Reference Clocks

The clock driver selected should provide a high quality reference clock with low phase noise and cycle-to-cycle jitter. Phase noise less than 100 kHz can be tracked by the PLL and data recovery loops and is less of a problem. Phase noise above 15 MHz is filtered by the PLL. The most problematic phase noise occurs in the 1–15 MHz range. The source impedance of the clock driver should be 50  $\Omega$  to match the transmission line and reduce reflections which are a source of noise to the system.

Table 57 describes some AC parameters common to SGMII, and PCI Express protocols.

Parameter	Symbol	Min	Max	Unit	Notes
Rising Edge Rate	Rise Edge Rate	1.0	4.0	V/ns	2, 3
Falling Edge Rate	Fall Edge Rate	1.0	4.0	V/ns	2, 3
Differential Input High Voltage	V <sub>IH</sub>	+200	_	mV	2
Differential Input Low Voltage	V <sub>IL</sub>	_	-200	mV	2
Rising edge rate (SD <i>n</i> _REF_CLK) to falling edge rate (SD <i>n</i> _REF_CLK) matching	Rise-Fall Matching	_	20	%	1, 4

#### Table 57. SerDes Reference Clock Common AC Parameters

#### Notes:

- 1. Measurement taken from single ended waveform.
- 2. Measurement taken from differential waveform.
- 3. Measured from –200 mV to +200 mV on the differential waveform (derived from SD*n*\_REF\_CLK minus SD*n*\_REF\_CLK). The signal must be monotonic through the measurement region for rise and fall time. The 400 mV measurement window is centered on the differential zero crossing. See Figure 53.
- 4. Matching applies to rising edge rate for SDn\_REF\_CLK and falling edge rate for SDn\_REF\_CLK. It is measured using a 200 mV window centered on the median cross point where SDn\_REF\_CLK rising meets SDn\_REF\_CLK falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations. The rise edge rate of SDn\_REF\_CLK should be compared to the fall edge rate of SDn\_REF\_CLK, the maximum allowed difference should not exceed 20% of the slowest edge rate. See Figure 54.



Figure 53. Differential Measurement Points for Rise and Fall Time



High-Speed Serial Interfaces (HSSI)



Figure 54. Single-Ended Measurement Points for Rise and Fall Time Matching

The other detailed AC requirements of the SerDes reference clocks is defined by each interface protocol based on application usage. Refer to the following sections for detailed information:

- Section 8.3.1, "The DBWO Signal"
- Section 17.2, "AC Requirements for PCI Express SerDes Clocks"

### 16.2.4.1 Spread Spectrum Clock

SD1\_REF\_CLK/SD1\_REF\_CLK were designed to work with a spread spectrum clock (+0 to -0.5% spreading at 30–33 kHz rate is allowed), assuming both ends have same reference clock. For better results, a source without significant unintended modulation should be used.

SD2\_REF\_CLK/SD2\_REF\_CLK are not intended to be used with, and should not be clocked by, a spread spectrum clock source.

# 16.3 SerDes Transmitter and Receiver Reference Circuits

Figure 55 shows the reference circuits for SerDes data lane's transmitter and receiver.



Figure 55. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in the section below (PCI Express or SGMII) in this document based on the application usage:

- Section 8.3, "SGMII Interface Electrical Characteristics"
- Section 17, "PCI Express"

Please note that external AC Coupling capacitor is required for the above serial transmission protocols with the capacitor value defined in specification of each protocol section.





# 18.3 Pinout Listings

Table 62 provides the pinout listing for the MPC8544E 783 FC-PBGA package.

#### NOTE

The naming convention of TSEC1 and TSEC3 is used to allow the splitting voltage rails for the eTSEC blocks and to ease the port of existing PowerQUICC III software.

### NOTE

The DMA\_DACK[0:1] and TEST\_SEL pins must be set to a proper state during POR configuration. Please refer to Table 62 for more details.

Signal	Package Pin Number	Pin Type	Power Supply	Notes
	PCI			
PCI1_AD[31:0]	AE8, AD8, AF8, AH12, AG12, AB9, AC9, AE9, AD10, AE10, AC11, AB11, AB12, AC12, AF12, AE11, Y14, AE15, AC15, AB15, AA15, AD16, Y15, AB16, AF18, AE18, AC17, AE19, AD19, AB17, AB18, AA16	I/O	OV <sub>DD</sub>	
PCI1_C_BE[3:0]	AC10, AE12, AA14, AD17	I/O	OV <sub>DD</sub>	—
PCI1_GNT[4:1]	AE7, AG11,AH11, AC8	0	OV <sub>DD</sub>	4, 8, 24
PCI1_GNT0	AE6	I/O	OV <sub>DD</sub>	—
PCI1_IRDY	AF13	I/O	OV <sub>DD</sub>	2
PCI1_PAR	AB14	I/O	OV <sub>DD</sub>	—
PCI1_PERR	AE14	I/O	OV <sub>DD</sub>	2
PCI1_SERR	AC14	I/O	OV <sub>DD</sub>	2
PCI1_STOP	AA13	I/O	OV <sub>DD</sub>	2
PCI1_TRDY	AD13	I/O	OV <sub>DD</sub>	2
PCI1_REQ[4:1]	AF9, AG10, AH10, AD6	I	OV <sub>DD</sub>	—
PCI1_REQ0	AB8	I/O	OV <sub>DD</sub>	—
PCI1_CLK	AH26	I	OV <sub>DD</sub>	—
PCI1_DEVSEL	AC13	I/O	OV <sub>DD</sub>	2
PCI1_FRAME	AD12	I/O	OV <sub>DD</sub>	2
PCI1_IDSEL	AG6	l	OV <sub>DD</sub>	—

#### Table 62. MPC8544E Pinout Listing



Signal	Package Pin Number	Pin Type	Power Supply	Notes
LCS6/DMA_DACK2	J16	0	BV <sub>DD</sub>	1
LCS7/DMA_DDONE2	L18	0	BV <sub>DD</sub>	1
LWE0/LBS0/LSDDQM[0]	J22	0	BV <sub>DD</sub>	4, 8
LWE1/LBS1/LSDDQM[1]	H22	0	BV <sub>DD</sub>	4, 8
LWE2/LBS2/LSDDQM[2]	H23	0	BV <sub>DD</sub>	4, 8
LWE3/LBS3/LSDDQM[3]	H21	0	BV <sub>DD</sub>	4, 8
LALE	J26	0	BV <sub>DD</sub>	4, 7, 8
LBCTL	J25	0	BV <sub>DD</sub>	4, 7, 8
LGPL0/LSDA10	J20	0	BV <sub>DD</sub>	4, 8
LGPL1/LSDWE	К20	0	BV <sub>DD</sub>	4, 8
LGPL2/LOE/LSDRAS	G20	0	BV <sub>DD</sub>	4, 7, 8
LGPL3/LSDCAS	H18	0	BV <sub>DD</sub>	4, 8
LGPL4/LGTA/LUPWAIT/ LPBSE	L20	I/O	BV <sub>DD</sub>	28
LGPL5	К19	0	BV <sub>DD</sub>	4, 8
LCKE	L17	0	BV <sub>DD</sub>	—
LCLK[0:2]	H24, J24, H25	0	BV <sub>DD</sub>	—
LSYNC_IN	D27	I	BV <sub>DD</sub>	—
LSYNC_OUT	D28	0	BV <sub>DD</sub>	—
	DMA			
DMA_DACK[0:1]	Y13, Y12	0	OV <sub>DD</sub>	4, 8, 9
DMA_DREQ[0:1]	AA10, AA11	I	OV <sub>DD</sub>	—
DMA_DDONE[0:1]	AA7, Y11	0	OV <sub>DD</sub>	—
	Programmable Interrupt Contro	oller		·
UDE	AH15	I	OV <sub>DD</sub>	—
MCP	AG18	I	OV <sub>DD</sub>	—
IRQ[0:7]	AG22, AF17, AD21, AF19, AG17, AF16, AC23, AC22	I	OV <sub>DD</sub>	_
IRQ[8]	AC19	I	OV <sub>DD</sub>	—
IRQ[9]/DMA_DREQ3	AG20	I	OV <sub>DD</sub>	1
IRQ[10]/DMA_DACK3	AE27	I/O	OV <sub>DD</sub>	1
IRQ[11]/DMA_DDONE3	AE24	I/O	OV <sub>DD</sub>	1
IRQ_OUT	AD14	0	OV <sub>DD</sub>	2

#### Table 62. MPC8544E Pinout Listing (continued)



Package Description

#### Table 62. MPC8544E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
SD2_REF_CLK	AF2	I	XV <sub>DD</sub>	_
SD2_TST_CLK	AG4	_	—	_
SD2_TST_CLK	AF4	_	—	_
	General-Purpose Output			
GPOUT[0:7]	AF22, AH23, AG27, AH25, AF21, AF25, AG26, AF26	0	OV <sub>DD</sub>	_
	General-Purpose Input			•
GPIN[0:7]	AH24, AG24, AD23, AE21, AD22, AF23, AG25, AE20	I	OV <sub>DD</sub>	_
	System Control		I	1
HRESET	AG16	I	OV <sub>DD</sub>	
HRESET_REQ	AG15	0	OV <sub>DD</sub>	21
SRESET	AG19	I	OV <sub>DD</sub>	
CKSTP_IN	AH5	I	OV <sub>DD</sub>	—
CKSTP_OUT	AA12	0	OV <sub>DD</sub>	2, 4
	Debug			
TRIG_IN	AC5	I	OV <sub>DD</sub>	—
TRIG_OUT/READY/ QUIESCE	AB5	0	OV <sub>DD</sub>	5, 8, 15, 21
MSRCID[0:1]	Y7, W9	0	OV <sub>DD</sub>	4, 5, 8
MSRCID[2:4]	AA9, AB6, AD5	0	OV <sub>DD</sub>	5, 15, 21
MDVAL	Y8	0	OV <sub>DD</sub>	5
CLK_OUT	AE16	0	OV <sub>DD</sub>	10
	Clock			
RTC	AF15	I	OV <sub>DD</sub>	—
SYSCLK	AH16	I	OV <sub>DD</sub>	—
	JTAG			
тск	AG28	I	OV <sub>DD</sub>	—
TDI	AH28	I	OV <sub>DD</sub>	11
TDO	AF28	0	OV <sub>DD</sub>	10
TMS	AH27	I	OV <sub>DD</sub>	11
TRST	AH22	I	OV <sub>DD</sub>	11



Signal	Package Pin Number	Pin Type	Power Supply	Notes
AVDD_SRDS	W28	Power for SRDSPLL (1.0 V)	_	19
AVDD_SRDS2	AG1	Power for SRDSPLL (1.0 V)	_	19
SENSEVDD	W11	0	V <sub>DD</sub>	12
SENSEVSS	W10	—	_	12
	Analog Signals			
MVREF	A28	Reference voltage signal for DDR	MVREF	_
SD1_IMP_CAL_RX	M26	—	200 $\Omega$ to GND	
SD1_IMP_CAL_TX	AE28	—	100 $\Omega$ to GND	_
SD1_PLL_TPA	V26		AVDD_SRDS ANALOG	17
SD2_IMP_CAL_RX	АНЗ	I	200 $\Omega$ to GND	
SD2_IMP_CAL_TX	Y1	I	100 $\Omega$ to GND	
SD2_PLL_TPA	AH1	0	AVDD_SRDS2 ANALOG	17
	No Connect Pins			
NC	C19, D7, D10, K13, L6, K9, B6, F12, J7, M19, M25, N19, N24, P19, R19, AB19, T12, W3, M12, W5, P12, T19, W1, W7, L13, U19, W4, V8, V9, V10, V11, V12, V13, V14, V15, V16, V17, V18, V19, W2, W6, W8, T11, U11, W12, W13, W14, W15, W16, W17, W18, W19, W27, V25, Y17, Y18, Y19, AA18, AA19, AB20, AB21, AB22, AB23, J9	_	_	_

Notes:

1.All multiplexed signals are listed only once and do not re-occur. For example, LCS5/DMA\_REQ2 is listed only once in the Local Bus Controller Interface section, and is not mentioned in the DMA section even though the pin also functions as DMA\_REQ2.

2. Recommend a weak pull-up resistor (2–10 K $\Omega$ ) be placed on this pin to OV<sub>DD</sub>.

3. This pin must always be pulled high.

4. This pin is a reset configuration pin. It has a weak internal pull-up P-FET which is enabled only when the processor is in the reset state. This pull-up is designed such that it can be overpowered by an external 4.7-kΩ pull-down resistor. However, if the signal is intended to be high after reset, and if there is any device on the net which might pull down the value of the net at reset, then a pull-up or active driver is needed. TSEC3\_TXD[3] (cfg\_srds\_sgmii\_refclk) is an exception, because the default value of this configuration signal is low (0). Thus, no external pull-down resistor is needed for selecting the default configuration value.

5. Treat these pins as no connects (NC) unless using debug address functionality.



Table 71 provides the thermal resistance with heat sink in open flow.

Heat Sink with Thermal Grease	Air Flow	Thermal Resistance (°C/W)
Wakefield $53 \times 53 \times 25$ mm pin fin	Natural convection	6.1
Wakefield $53 \times 53 \times 25$ mm pin fin	1 m/s	3.0
Aavid $35 \times 31 \times 23$ mm pin fin	Natural convection	8.1
Aavid $35 \times 31 \times 23$ mm pin fin	1 m/s	4.3
Aavid $30 \times 30 \times 9.4$ mm pin fin	Natural convection	11.6
Aavid $30 \times 30 \times 9.4$ mm pin fin	1 m/s	6.7
Aavid $43 \times 41 \times 16.5$ mm pin fin	Natural convection	8.3
Aavid $43 \times 41 \times 16.5$ mm pin fin	1 m/s	4.3

Table 71. Thermal Resistance with Heat Sink in Open Flow

Simulations with heat sinks were done with the package mounted on the 2s2p thermal test board. The thermal interface material was a typical thermal grease such as Dow Corning 340 or Wakefield 120 grease. For system thermal modeling, the MPC8544E thermal model without a lid is shown in Figure 60. The substrate is modeled as a block  $29 \times 29 \times 1.18$  mm with an in-plane conductivity of 18.0 W/m•K and a through-plane conductivity of 1.0 W/m•K. The solder balls and air are modeled as a single block  $29 \times 29 \times 0.58$  mm with an in-plane conductivity of 0.034 W/m•K and a through plane conductivity of 12.1 W/m•K. The die is modeled as  $7.6 \times 8.4$  mm with a thickness of 0.75 mm. The bump/underfill layer is modeled as a collapsed thermal resistance between the die and substrate assuming a conductivity of 6.5 W/m•K in the thickness dimension of 0.07 mm. The die is centered on the substrate. The thermal model uses approximate dimensions to reduce grid. Please refer to Figure 59 for actual dimensions.

# 20.2 Recommended Thermal Model

Table 72 shows the MPC8544E thermal model.

Table 72. MPC	C8544EThermal Model
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Conductivity Value		Units			
	Die (7.6 × 8.4 × 0.75mm)				
Silicon	Temperature dependent	_			
Bump/l	al Resistance				
Kz	6.5	W/m∙K			
Substrate (29 × 29 × 1.18 mm)					
Кх	18	W/m∙K			
Ку	18				
Kz	1.0				



Note the following:

- AV<sub>DD</sub> SRDS should be a filtered version of SV<sub>DD</sub>.
- Signals on the SerDes interface are fed from the XV<sub>DD</sub> power plane.

# 21.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8544E system, and the device itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each  $V_{DD}$ ,  $TV_{DD}$ ,  $BV_{DD}$ ,  $OV_{DD}$ ,  $GV_{DD}$ , and  $LV_{DD}$  pin of the device. These decoupling capacitors should receive their power from separate  $V_{DD}$ ,  $TV_{DD}$ ,  $BV_{DD}$ ,  $OV_{DD}$ ,  $TV_{DD}$ ,  $BV_{DD}$ ,  $OV_{DD}$ ,  $GV_{DD}$ , and  $LV_{DD}$ ; and GND power planes in the PCB, utilizing short low impedance traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1  $\mu$ F. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the  $V_{DD}$ ,  $TV_{DD}$ ,  $BV_{DD}$ ,  $OV_{DD}$ ,  $GV_{DD}$ , and  $LV_{DD}$  planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330  $\mu$ F (AVX TPS tantalum or Sanyo OSCON). However, customers should work directly with their power regulator vendor for best values and types and quantity of bulk capacitors.

# 21.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power ( $SV_{DD}$  and  $XV_{DD}$ ) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

- First, the board should have at least 10 × 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the device. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the device as close to the supply and ground connections as possible.
- Second, there should be a  $1-\mu F$  ceramic chip capacitor on each side of the device. This should be done for all SerDes supplies.
- Third, between the device and any SerDes voltage regulator there should be a  $10-\mu$ F, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a  $100-\mu$ F, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.



resistance of the pull-up devices.  $R_P$  and  $R_N$  are designed to be close to each other in value. Then,  $Z_0 = (R_P + R_N) \div 2$ .



Figure 67. Driver Impedance Measurement

Table 73 summarizes the signal impedance targets. The driver impedances are targeted at minimum  $V_{DD}$ , nominal  $OV_{DD}$ , 90°C.

 Table 73. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R <sub>N</sub>	43 Target	25 Target	20 Target	Z <sub>0</sub>	W
R <sub>P</sub>	43 Target	25 Target	20 Target	Z <sub>0</sub>	W

Note: Nominal supply voltages. See Table 1.

# 21.8 Configuration Pin Muxing

The MPC8544E provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 k $\Omega$  on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While  $\overline{\text{HRESET}}$  is asserted however, these pins are treated as inputs. The value presented on these pins while  $\overline{\text{HRESET}}$  is asserted, is latched when  $\overline{\text{HRESET}}$  deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Most of these sampled configuration pins are equipped with an on-chip gated resistor of approximately 20 kΩ. This value should permit the 4.7-kΩ resistor to pull the configuration pin to a valid logic low level. The pull-up resistor is enabled only during  $\overline{\text{HRESET}}$  (and for platform /system clocks after  $\overline{\text{HRESET}}$  deassertion to ensure capture of the reset value). When the input receiver is disabled the pull-up is also, thus allowing functional operation of the pin as an output with minimal signal quality or delay disruption. The default value for all configuration bits treated this way has